



#5/Amended
PATENT
Customer No. 22,852

Attorney Docket No. 04329/2222
2/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
)
Kouji MATSUO, et al.) Group Art Unit: 2814
)
Serial No.: 09/492,780) Examiner: Rao, Shrinivas H.
)
Filed: January 28, 2000)
)
For: SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURING)
THE SAME)

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Office Action dated November 4, 2002, with a period for response extending through February 4, 2003, Applicants amend the application as follows, and respectfully request the Examiner's reconsideration in view of the following remarks:

IN THE CLAIMS:

Please amend claim 12 as follows:

12. (Three Times Amended) A semiconductor device, comprising:
- a semiconductor substrate;
 - a metal-containing insulating film formed directly or indirectly on said semiconductor substrate, said metal-containing insulating film including a plurality of first insulating regions each of which is formed of a grain containing a metal oxide and a second insulating region

DI
FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com